MSA-1110

Cascadable Silicon Bipolar MMIC Amplifier



Data Sheet

Description

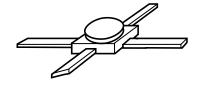
The MSA-1110 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic high reliability package. This MMIC is designed for high dynamic range in either 50 or 75Ω systems by combining low noise figure with high IP₃. Typical applications include narrow and broadband linear amplifiers in industrial and military systems.

The MSA-series is fabricated using Avago's 10 GHz f_T , 25 GHz f_{MAX} silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

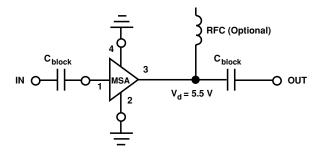
Features

- High Dynamic Range Cascadable 50Ω or 75Ω Gain Block
- 3 dB Bandwidth: 50 MHz to 1.6 GHz
- 17.5 dBm Typical P_{1 dB} at 0.5 GHz
- 12 dB Typical 50 Ω Gain at 0.5 GHz
- 3.5 dB Typical Noise Figure at 0.5 GHz
- Hermetic Gold-ceramic Microstrip Package

100 mil Package



Typical Biasing Configuration



MSA-1110 Absolute Maximum Ratings

Parameter	Absolute Maximum ^[1]		
Device Current	90 mA		
Power Dissipation ^[2,3]	560 mW		
RF Input Power	+13 dBm		
Junction Temperature	200°C		
Storage Temperature	−65 to 200°C		

Thermal Resistance^[2, 4]:

 $\theta_{ic} = 135$ °C/W

- 1. Permanent damage may occur if any of these limits are exceeded.
- T_{CASE} = 25°C.
 Derate at 7.4 mW/°C for T_C > 124°C.
- 4. The small spot size of this technique results in a higher, though more accurate determination of θ_{ic} than do alternate methods.

Electrical Specifications^[1], $T_A = 25^{\circ}C$

Symbol	Parameters and Test Conditions: $I_d = 60$	Units	Min.	Тур.	Max.	
G _P	Power Gain (S ₂₁ ²)	f = 0.1 GHz	dB	11.5	12.5	13.5
ΔG_P	Gain Flatness	f = 0.1 to 1.0 GHz	dB		±0.7	±1.0
f _{3 dB}	3 dB Bandwidth ^[2]		GHz		1.6	
VCMD	Input VSWR	f = 0.1 to 1.0 GHz			1.7:1	
VSWR —	Output VSWR	f = 0.1 to 1.0 GHz			1.9:1	
NF	50 Ω Noise Figure	f = 0.5 GHz	dB		3.5	4.5
P _{1 dB}	Output Power at 1 dB Gain Compression	f = 0.5 GHz	dBm	16.0	17.5	
IP ₃	Third Order Intercept Point	f = 0.5 GHz	dBm		30.0	
t _D	Group Delay	f = 0.5 GHz	psec		160	
V _d	Device Voltage		V	4.5	5.5	6.5
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-8.0	

Notes:

2. Referenced from 50 MHz gain (GP).

^{1.} The recommended operating current range for this device is 40 to 75 mA. Typical performance as a function of current is on the following page.

MSA-1110 Typical Scattering Parameters (Z $_0$ = 50 Ω , T_A = 25°C, I_d = 60 mA)

Freq.	9	S ₁₁		S ₂₁			S ₁₂		S	22	
GHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	k
.0005	.83	-7	19.5	9.44	176	-31.9	.025	39	.84	-7	0.77
.005	.54	-50	16.8	6.92	158	-18.7	.116	34	.55	-50	0.60
.025	.15	–78	13.0	4.47	167	-16.6	.148	9	.15	-79	1.03
.050	.10	-64	12.6	4.26	171	-16.5	.149	5	.10	-67	1.08
.100	.08	-63	12.5	4.23	171	-16.5	.150	4	.08	-66	1.09
.200	.09	-74	12.4	4.17	166	-16.4	.152	4	.09	-78	1.09
.300	.11	-85	12.3	4.10	160	-16.2	.154	5	.12	-89	1.07
.400	.13	-94	12.3	4.10	154	-16.1	.157	6	.15	-98	1.05
.500	.16	-102	12.1	4.04	148	-15.9	.161	7	.18	-106	1.02
.600	.18	-108	12.0	3.98	143	-15.6	.165	8	.20	-113	1.00
.700	.21	-114	11.8	3.89	137	-15.4	.169	8	.23	-120	0.97
.800	.23	-120	11.6	3.80	131	-15.2	.173	8	.25	-126	0.95
.900	.25	-126	11.4	3.71	126	-15.0	.178	8	.28	-132	0.92
1.000	.27	-131	11.1	3.60	120	-14.8	.182	8	.30	-137	0.91
1.500	.36	-153	9.8	3.10	96	-13.8	.203	4	.37	-160	0.83
2.000	.42	–171	8.4	2.64	74	-13.3	.217	1	.40	-178	0.82
2.500	.47	177	7.2	2.29	59	-12.5	.236	-2	.41	172	0.80
3.000	.47	159	5.9	1.97	43	-13.2	.220	-10	.38	157	0.95

Typical Performance, $T_A = 25^{\circ}C$, $Z_0 = 50~\Omega$

(unless otherwise noted)

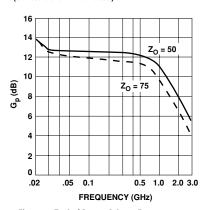


Figure 1. Typical Power Gain vs. Frequency, $I_d = 60 \text{ mA}$.

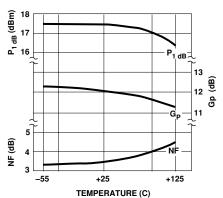


Figure 4. Output Power at 1 dB Gain Compression, Noise Figure and Power Gain vs. Case Temperature, $f=0.5~{\rm GHz}$, $I_d=60~{\rm mA}.$

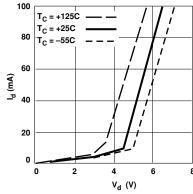


Figure 2. Device Current vs. Voltage.

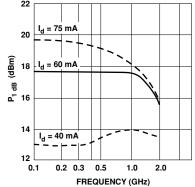


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

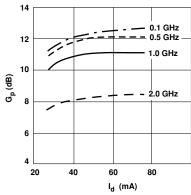


Figure 3. Power Gain vs. Current.

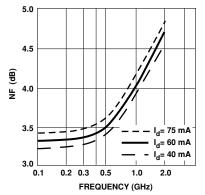


Figure 6. Noise Figure vs. Frequency.

Ordering Information

Part Numbers	No. of Devices	Comments		
MSA-1110	100	Bulk		

100 mil Package Dimensions

